

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSV)

## 2SK2382

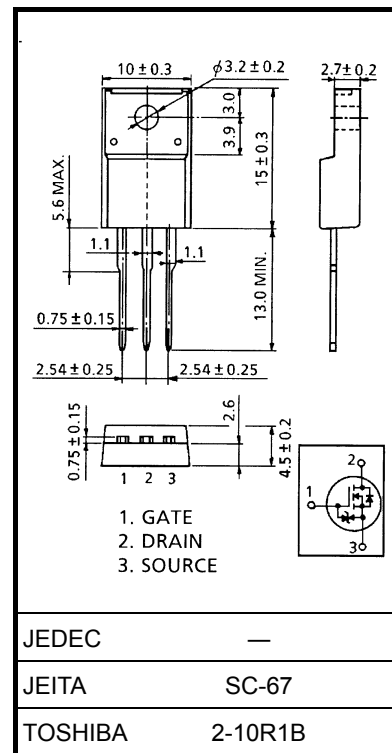
Switching Regulator, DC-DC Converter and Motor Drive Applications

Unit: mm

- Low drain-source ON resistance :  $R_{DS(ON)} = 0.13 \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 17 S$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \mu A$  (max) ( $V_{DS} = 200 V$ )
- Enhancement mode :  $V_{th} = 1.5 \sim 3.5 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

### Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	200	V
Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )	$V_{DGR}$	200	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	15 A
	Pulse (Note 1)	$I_{DP}$	45 A
Drain power dissipation ( $T_c = 25^\circ C$ )	$P_D$	45	W
Single pulse avalanche energy (Note 2)	$E_{AS}$	166	mJ
Avalanche current	$I_{AR}$	15	A
Repetitive avalanche energy (Note 3)	$E_{AR}$	4.5	mJ
Channel temperature	$T_{ch}$	150	$^\circ C$
Storage temperature range	$T_{stg}$	$-55 \sim 150$	$^\circ C$



Weight: 1.9 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	2.78	$^\circ C / W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	62.5	$^\circ C / W$

Note 1: Ensure that the channel temperature does not exceed  $150^\circ C$ .

Note 2:  $V_{DD} = 50 V, T_{ch} = 25^\circ C$  (initial),  $L = 1.2 mH, R_G = 25 \Omega, I_{AR} = 15 A$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.

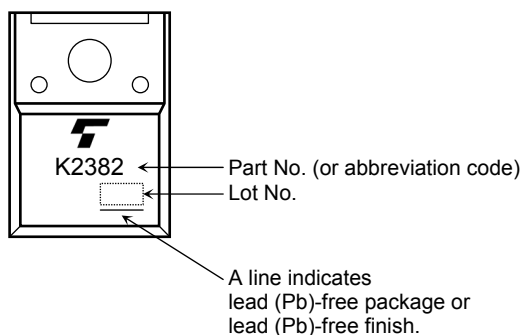
## Electrical Characteristics (Ta = 25°C)

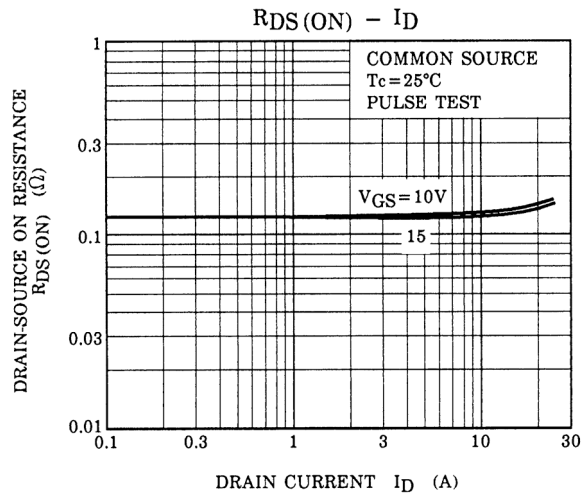
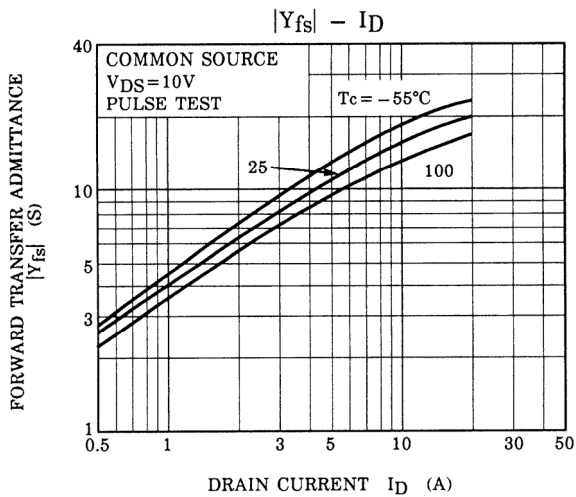
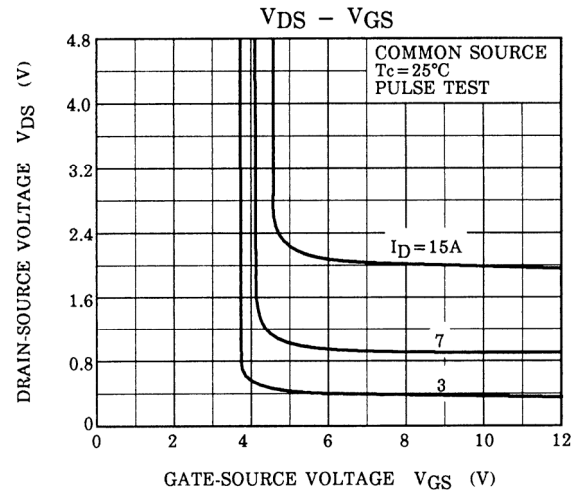
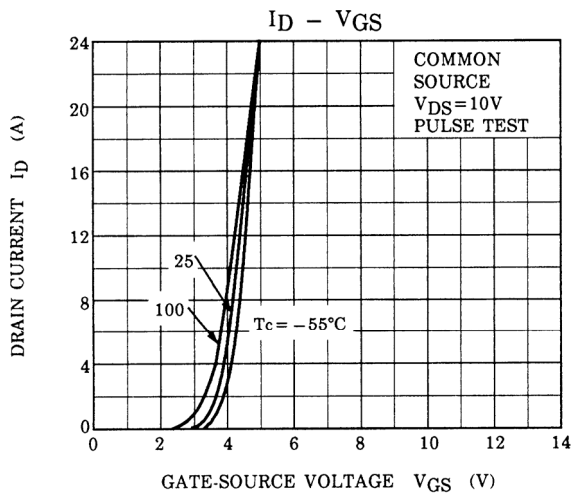
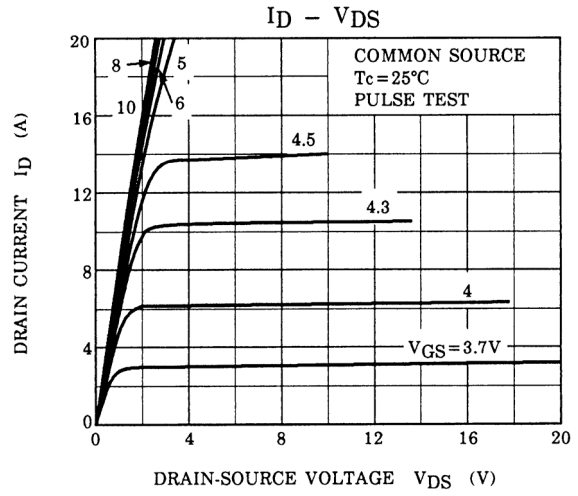
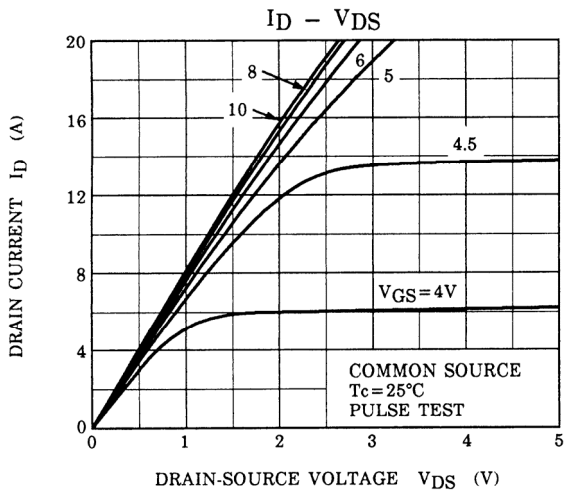
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current		$I_{DSS}$	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	200	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.5	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	—	0.13	0.18	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 10\text{ A}$	10	17	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	2000	—	pF
Reverse transfer capacitance		$C_{rss}$		—	200	—	
Output capacitance		$C_{oss}$		—	600	—	
Switching time	Rise time	$t_r$	<p><math>I_D = 10\text{ A}</math>  <math>V_{GS} = 10\text{ V}, 0\text{ V}</math>  <math>4.7\Omega</math>  <math>R_L = 10\Omega</math>  <math>V_{DD} = 100\text{ V}</math>  <math>V_{OUT}</math>  <math>Duty \leq 1\%, t_w = 10\mu\text{s}</math></p>	—	35	—	ns
	Turn-on time	$t_{on}$		—	50	—	
	Fall time	$t_f$		—	10	—	
	Turn-off time	$t_{off}$		—	66	—	
Total gate charge (Gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 15\text{ A}$	—	40	—	nC
Gate-source charge		$Q_{gs}$		—	25	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	15	—	

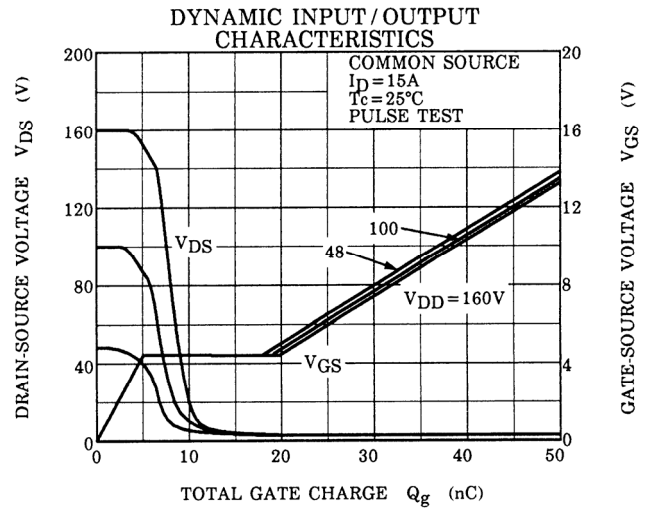
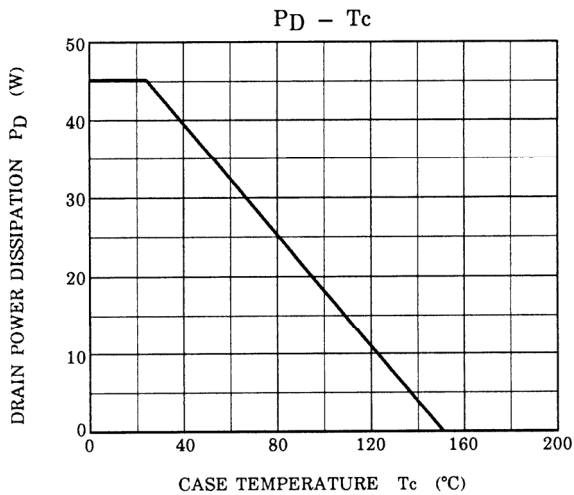
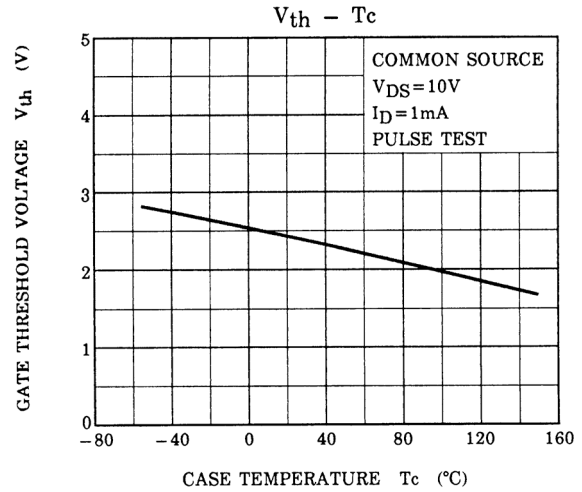
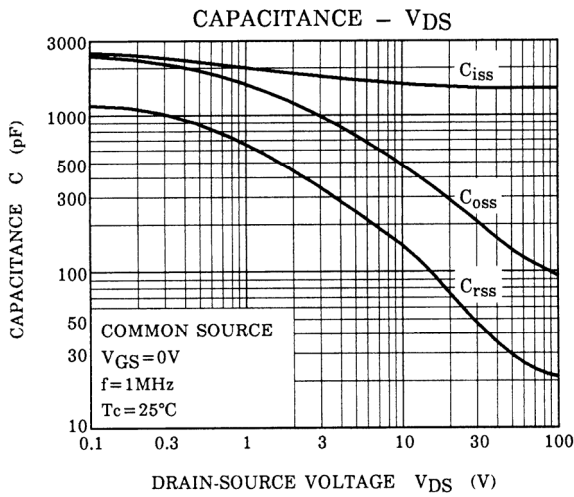
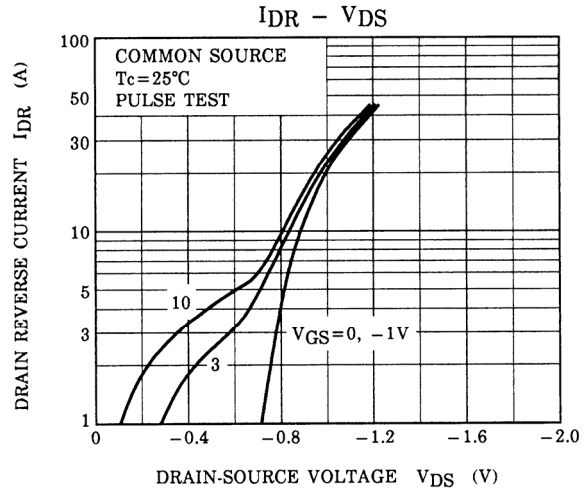
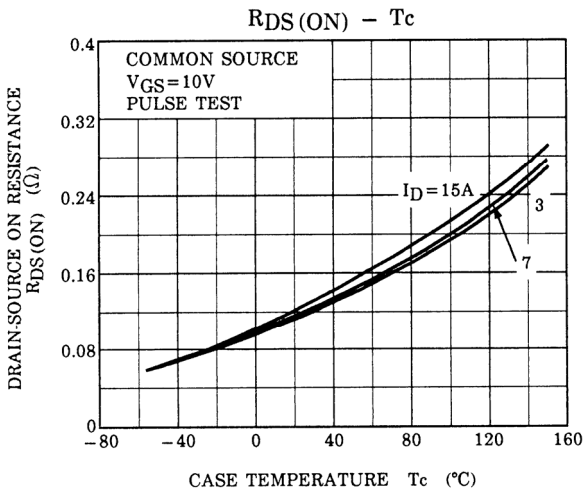
## Source-Drain Ratings and Characteristics (Ta = 25°C)

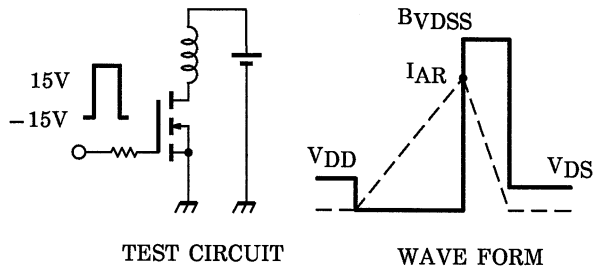
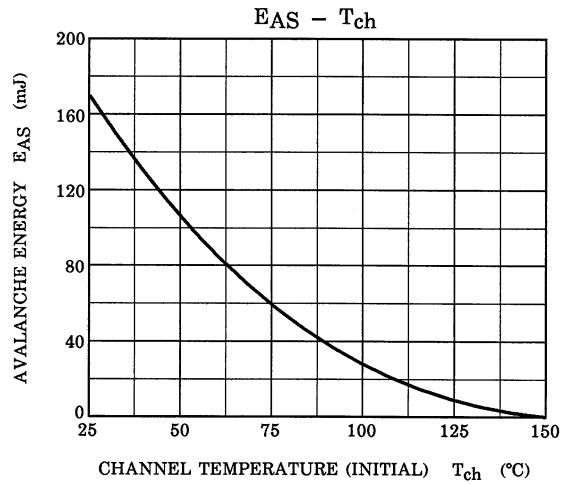
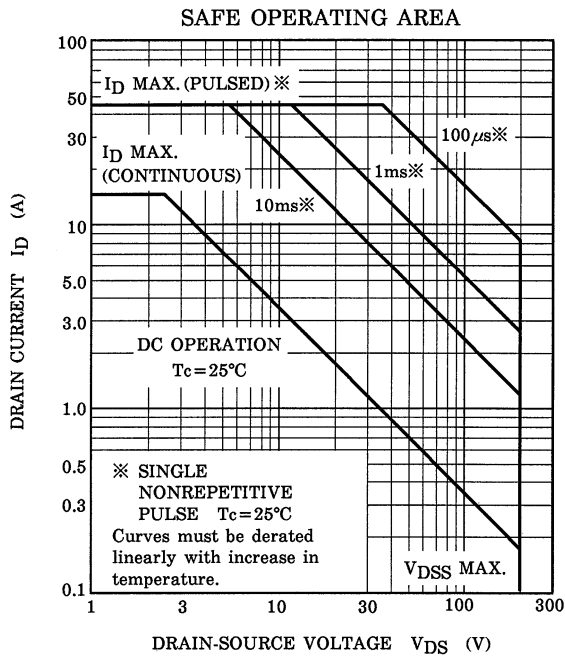
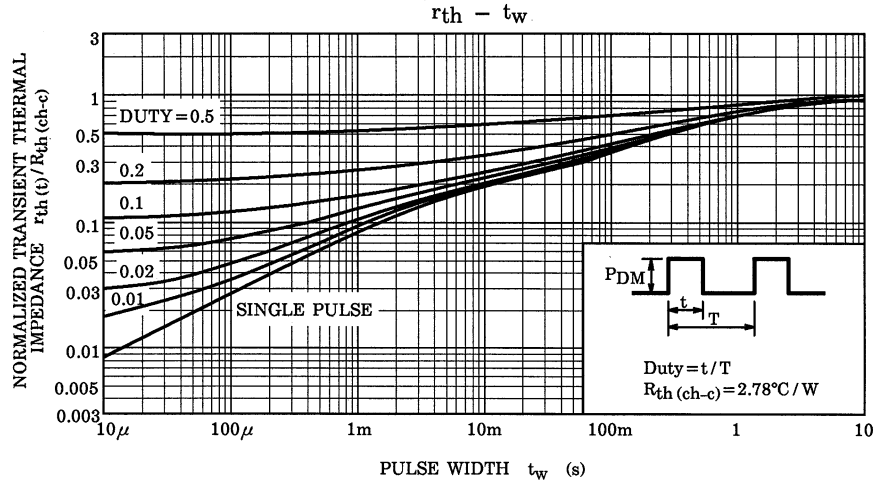
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	15	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	45	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 15\text{ A}, V_{GS} = 0\text{ V}$	—	—	-2.0	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 15\text{ A}, V_{GS} = 0\text{ V}$ $di_{DR} / dt = 100\text{ A} / \mu\text{s}$	—	180	—	ns
Reverse recovered charge	$Q_{rr}$		—	1.13	—	$\mu\text{C}$

## Marking









$R_G = 25 \Omega$   
 $V_{DD} = 50 \text{ V}, L = 1.2 \text{ mH}$

$$EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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